

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS : Satoru HANZAWA et al.
SERIAL NO. : (Con. of 10/201,317) GROUP ART UNIT: 2818
FILED : 24 June 2003 EXAMINER: Viet D. Nguyen
FOR : SEMICONDUCTOR DEVICE

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PRELIMINARY AMENDMENT

SIR:

Prior to examination of the above-identified continuation application, please enter the following amendment:

In the Specification:

Please amend the specification as follows:

*OK
W
BML*
Page 1: After the title, insert: This is a continuation of application number 10/201,317 ^{now US. Patent No. 6,611,474} filed 24 July 2002, which is a division of application number 09/706,374 filed 3 November 2000, the contents of which are incorporated herein by reference in their entirety.

Page 6: Replace the paragraph starting on line 13 with the following amended paragraph:

However, when a MOS transistor having the same ~~tox~~ oxidation film thickness (tox), as the peripheral transistors is used in sub-word drivers, the sub-word line voltage amplitude for the three values required for the capacitive coupling 2-transistor cell, as related above, is larger than the supply voltage amplitude so that the MOS transistor breakdown voltage problem is unavoidable.

Page 8: Replace the description of Fig. 16, lines 23-25, with the following amended description:

FIG. 16 is shows operation timing diagrams of the sub-word driver for generating the three value voltage levels of the third embodiment.

Pag 8: Replace the description of Fig. 17, lines 26-28, with the following amended description: